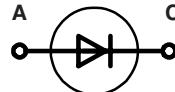


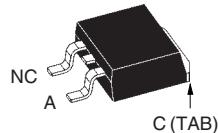
Fast Recovery Epitaxial Diode (FRED)

V_{RRM} = 600 V
I_{FAVM} = 20 A
t_{rr} = 35 ns

V _{RSM} V	V _{RRM} V	Type
600	600	DSEI 19-06AS



TO-263 AA

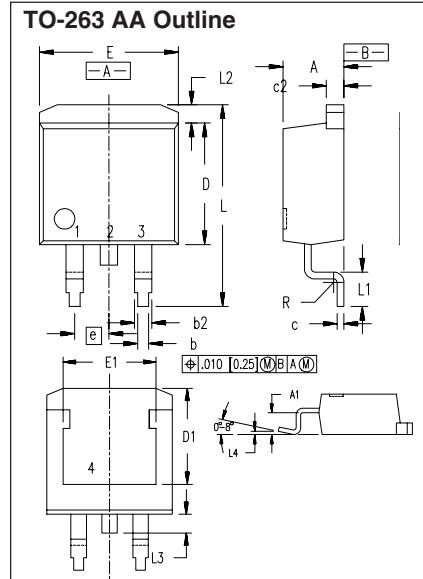


A = Anode, C = Cathode,
NC = No connection, TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I _{FRMS}	T _{VJ} = T _{VJM}	25	A
I _{FAVM} ①	T _C = 65°C; rectangular, d = 0.5	20	A
I _{FRM}	t _p < 10 µs; rep. rating, pulse width limited by T _{VJM}	150	A
I _{FSM}	T _{VJ} = 45°C; t = 10 ms (50 Hz), sine	100	A
	t = 8.3 ms (60 Hz), sine	110	A
	T _{VJ} = 150°C; t = 10 ms (50 Hz), sine	85	A
	t = 8.3 ms (60 Hz), sine	95	A
I ² t	T _{VJ} = 45°C t = 10 ms (50 Hz), sine	50	A ² s
	t = 8.3 ms (60 Hz), sine	50	A ² s
	T _{VJ} = 150°C; t = 10 ms (50 Hz), sine	36	A ² s
	t = 8.3 ms (60 Hz), sine	37	A ² s
T _{VJ}		-40...+150	°C
T _{VJM}		150	°C
T _{stg}		-40...+150	°C
P _{tot}	T _C = 25°C	61	W
Weight		2	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R	T _{VJ} = 25°C; V _R = V _{RRM}	50	µA
	T _{VJ} = 25°C; V _R = 0.8 • V _{RRM}	25	µA
	T _{VJ} = 125°C; V _R = 0.8 • V _{RRM}	3	mA
V _F	I _F = 16 A; T _{VJ} = 150°C	1.5	V
	T _{VJ} = 25°C	1.7	V
V _{T0}	For power-loss calculations only	1.12	V
r _T	T _{VJ} = T _{VJM}	23.2	mΩ
R _{thJC}		2	K/W
t _{rr}	I _F = 1 A; -di/dt = 50 A/µs; V _R = 30 V; T _{VJ} = 25°C	35	ns
I _{RM}	V _R = 350 V; I _F = 12 A; -di _F /dt = 100 A/µs L ≤ 0.05 µH; T _{VJ} = 100°C	4	4.4 A

① I_{FAVM} rating includes reverse blocking losses at T_{VJM}, V_R = 0.8 V_{RRM}, duty cycle d = 0.5
Data according to IEC 60747



Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.06	4.83	.160	.190
A1	2.03	2.79	.080	.110
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.46	0.74	.018	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	7.11	8.13	.280	.320
E	9.65	10.29	.380	.405
E1	6.86	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.38	0	.015
R	0.46	0.74	.018	.029

IXYS reserves the right to change limits, test conditions and dimensions

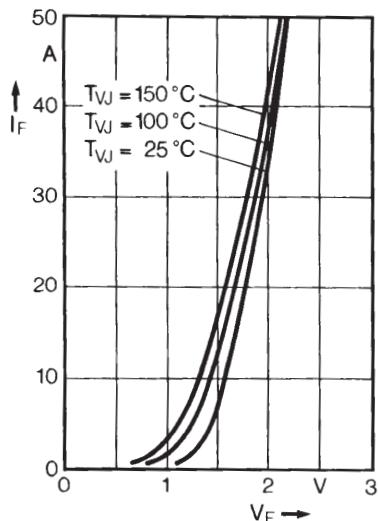


Fig. 1 Forward current versus voltage drop.

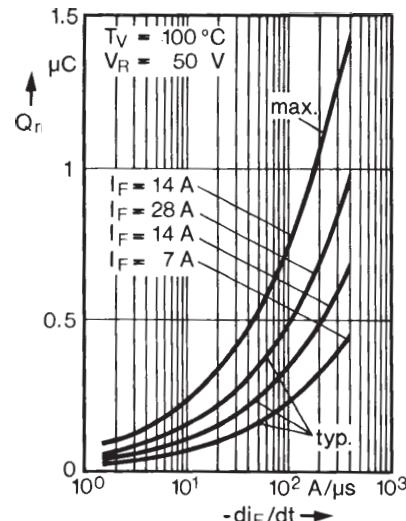


Fig. 2 Recovery charge versus $-di_F/dt$.

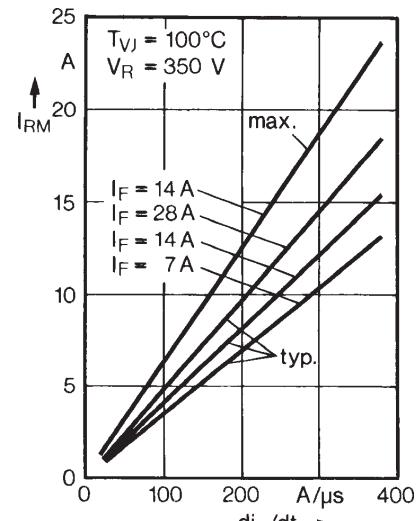


Fig. 3 Peak reverse current versus $-di_F/dt$.

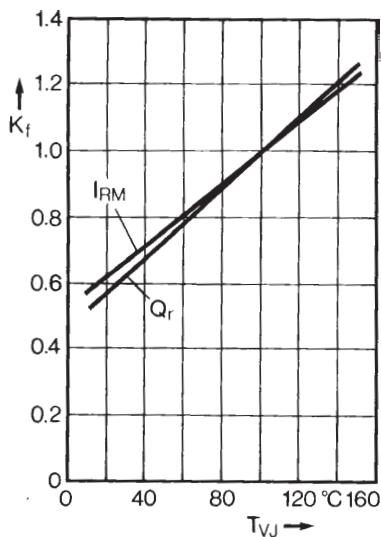


Fig. 4 Dynamic parameters versus junction temperature.

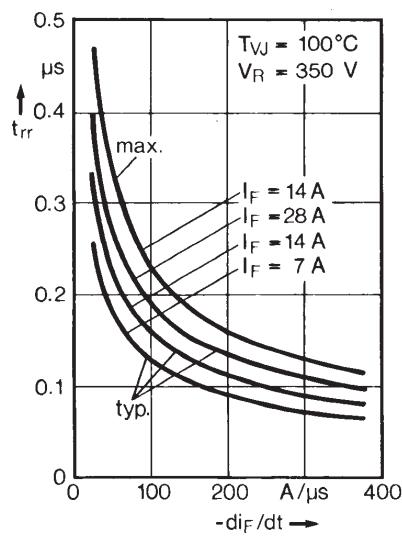


Fig. 5 Recovery time versus $-di_F/dt$.

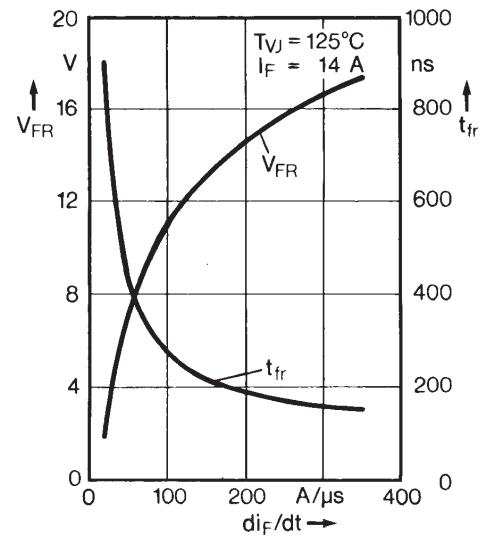


Fig. 6 Peak forward voltage versus di_F/dt .

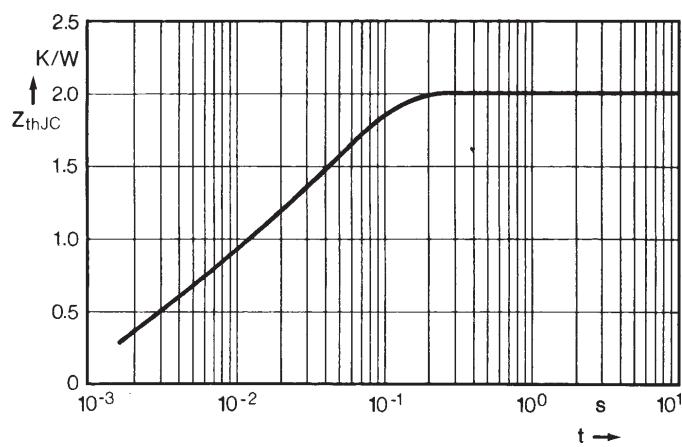


Fig. 7 Transient thermal impedance junction to case.

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